

Docket: CS 99 - 065CCB
S/N: 10/694,413

IFW



To: Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

From: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No.: 10/694,413	Filed: 10/27/2003
First Named Inventor: Kwok Keung Paul Ho	
Title: Plasma Etch Method For Forming Plasma Etched Silicon Layer	
Group Art Unit: 1763	Examiner: Goudreau, G. A.
Attorney Docket: CS 99-065CCB	

RESPONSE TO PATENT OFFICE ACTION

Dear Sir:

In response to the office action dated 06/24/2004, please consider the following remarks:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450, on ____

July 29, 2003.

Signature/Date

7/29/04

Stephen B. Ackerman
Reg. No. 37,761